	Туре	Hits	Search Text	DBs
<b>)</b>				US-PGPUB; USPAT; EPO; JPO;
لت	V & Z	4	(("53842/0") or ("5814859")).FN.	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT;
3				EPO; JPO;
_		20000	430 /\$.Ccis. (MOSFET)	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT;
<u>ب</u>	א מ מ	20	S2 and (silicon adj carbide adj	EPO; JPO;
•		-	MOSFET)	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT;
<u> </u>	0 0 0	3		EPO; JPO;
4		77		DERWENT;
	,			IBM_TDB
			41	US-PGPUB; USPAT;
ת	000			EPO; JPO;
Č		700100	#30 /\$.Ccis. (IVIOSEET)	DERWENT;
				IBM_TDB

	Туре	Hits	Search Text	DBs
				US-PGPUB; USPAT;
6	BRS	54	S5 and (silicon adj carbide adj MOSFET) and (ion adj implantation)	EPO; JPO; DERWENT;
				IBM_TDB
				:HASN ;BNGPG-SN
				EPO; JPO;
	UK U	N	so and (Ion ad) implantation adj mask)	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT;
				EPO; JPO;
C	070	4	So allo lallye	DERWENT;
				IBM_TDB
				:SPGPUB; USPAT)
	D O	<b>)</b>		EPO; JPO;
<b>U</b>	O NO			DERWENT;
				IBM_TDB
	-			:SPGPUB; USPAT;
				EPO; JPO;
-	O'NO	239130	430 /\$.CCIS. (IVIOSFET)	DERWENT;
				IBM_TDB

	Туре	Hits	Search Text	DBs
			S10 and (silicon adj carbide adj	US-PGPUB; USPAT EPO; JPO;
	מלע	C	MOSFET) and (implantation adj angle)	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT
3		2	S10 and (silicon adj carbide adj	EPO; JPO;
N	070	401		DERWENT;
				IBM_TDB
				US-PGPUB; USPAT
	000	>		EPO; JPO;
7	O NO		S IS and (angle ad) or adjimplantation)	DERWENT;
				IBM_TDB
				US-PGPUB; USPAT
		ת		EPO; JPO;
1	070	4		DERWENT;
				IBM_TDB
				US-PGPUB; USPAT
ע	מסמ	36177	"438"/\$.ccls. and (angloe of	EPO; JPO;
Č		00100	implantation)	DERWENT;
				IBM_TDB

	Туре	Hits	Search Text	DBs US-PGPUB; USPAT;
16	BRS	47516	"438"/\$.ccls. and (angle of implantation)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	0	S16 and (siliicon adj carbide adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	7447	S16 and (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	BRS	475	S18 and (SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	37	S19 and (vertical adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB